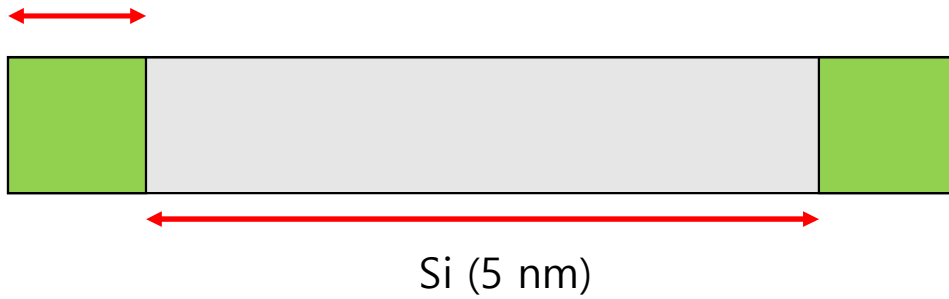


SiO (0.1 ~ 0.5 nm)



$$V_g = 0 \sim 1 \text{ V}$$

$$n_i = 1.075 \times 10^{16} \text{ m}^{-3}$$

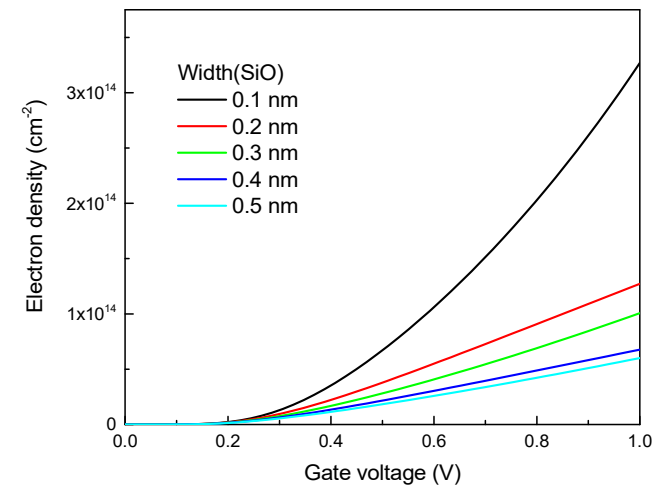
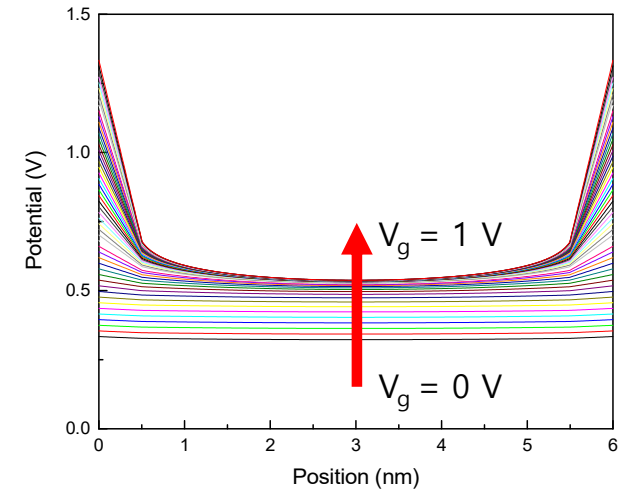
$$N_{\text{acc}} = 1 \times 10^{24} \text{ m}^{-3}$$

$$\epsilon_{\text{Si}} = 11.7\epsilon_0$$

$$\epsilon_{\text{SiO}} = 3.9\epsilon_0$$

The number of interval point = 500

The repetition of Newton method = 100



- As V_g increases, potential also increase.
- Integrated electron density increases drastically when gate voltage increases